8-input NAND gate Rev. 4 — 22 July 2015

Product data sheet

1. General description

The 74AHC30; 74AHCT30 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7-A.

The 74AHC30; 74AHCT30 provides an 8-input NAND function.

2. Features and benefits

- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than V_{CC}
- Input levels:
 - For 74AHC30: CMOS level
 - For 74AHCT30: TTL level
- ESD protection:
 - HBM JESD22-A114E exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

3. Ordering information

Table 1.Ordering information

Type number	Package				
	Temperature range	Name	Description	Version	
74AHC30D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads;	SOT108-1	
74AHCT30D			body width 3.9 mm		
74AHC30PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads;	SOT402-1	
74AHCT30PW			body width 4.4 mm		
74AHC30BQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very	SOT762-1	
74AHCT30BQ			thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm		
74AHC30GU12	-40 °C to +125 °C	XQFN12	plastic, extremely thin quad flat package; no leads; 12 terminals; body $1.70 \times 2.00 \times 0.50$ mm	SOT1174-1	

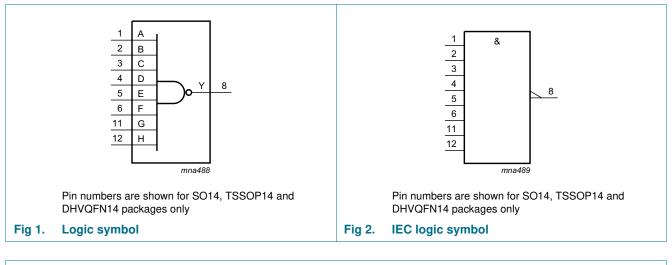


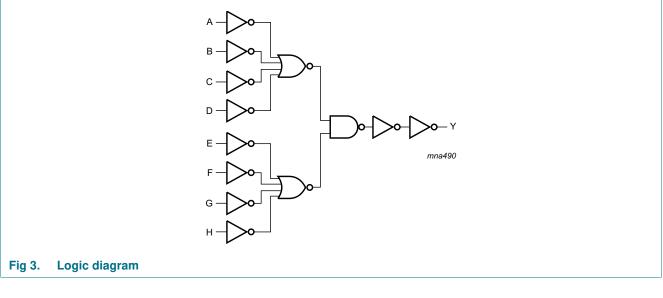
4. Marking

Table 2. Marking codes	
Type number	Marking
74AHC30D	74AHC30D
74AHCT30D	74AHCT30D
74AHC30PW	AHC30
74AHCT30PW	AHCT30
74AHC30BQ	AHC30
74AHCT30BQ	AHT30
74AHC30GU12	A3[1]

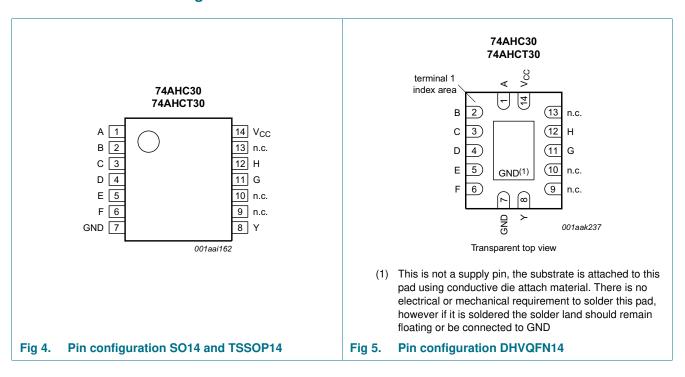
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

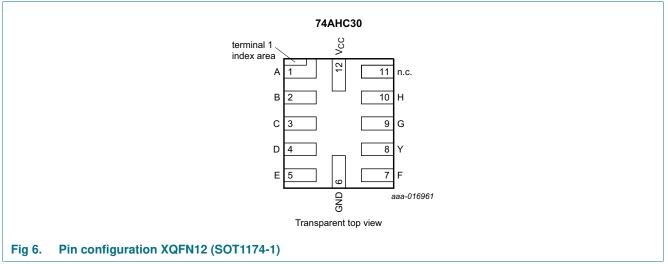




6. Pinning information







6.2 Pin description

Table 3.	Pin description		
Symbol	Pin		Description
	SO14, TSSOP14 and DHVQFN14	XQFN12	
A	1	1	data input
В	2	2	data input
С	3	3	data input
D	4	4	data input
E	5	5	data input
F	6	7	data input
GND	7	6	ground (0 V)
Y	8	8	data output
n.c.	9	-	not connected
n.c.	10	-	not connected
G	11	9	data input
Н	12	10	data input
n.c.	13	11	not connected
V _{CC}	14	12	supply voltage

7. Functional description

Table 4. Function table^[1]

Input								Output
Α	В	С	D	E	F	G	Н	Y
L	Х	Х	Х	Х	Х	Х	Х	Н
Х	L	Х	Х	Х	Х	Х	Х	Н
Х	Х	L	Х	Х	Х	Х	Х	Н
Х	Х	Х	L	Х	Х	Х	Х	Н
Х	Х	Х	Х	L	Х	Х	Х	Н
Х	Х	Х	Х	Х	L	Х	Х	Н
Х	Х	Х	Х	Х	Х	L	Х	Н
Х	Х	Х	Х	Х	Х	Х	L	Н
Н	Н	Н	Н	Н	Н	Н	Н	L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-0.5	+7.0	V
VI	input voltage			-0.5	+7.0	V
I _{IK}	input clamping current	V _I < -0.5 V	[1]	-20	-	mA
I _{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC}$ + 0.5 V	[1]	-20	+20	mA
lo	output current	$V_{O} = -0.5 \text{ V}$ to ($V_{CC} + 0.5 \text{ V}$)		-25	+25	mA
I _{CC}	supply current			-	+75	mA
I _{GND}	ground current			-75	-	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$				
		SO14, TSSOP14 and DHVQFN14	[2]	-	500	mW
		XQFN12		-	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

For SO14 packages: above 70 °C, the value of P_{tot} derates linearly at 8 mW/K.
 For TSSOP14 packages: above 60 °C, the value of P_{tot} derates linearly at 5.5 mW/K.
 For DHVQFN14 packages: above 60 °C, the value of P_{tot} derates linearly at 4.5 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-	74AHC30			74AHCT30		
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	0	-	5.5	V
Vo	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise	$V_{CC}=3.3~V\pm0.3~V$	-	-	100	-	-	-	ns/V
	and fall rate	$V_{CC}=5.0~V\pm0.5~V$	-	-	20	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C	;	–40 °C t	o +85 °C	–40 °C to +125 °C		Unit	
			Min	Тур	Max	Min	Max	Min	Max	-	
74AHC3	0	1				1		1	1		
VIH	HIGH-level	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V	
	input voltage	V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V	
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V	
V _{IL}	LOW-level	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V	
	input voltage	V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V	
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V	
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$									
	output voltage	$I_{O} = -50 \ \mu A; V_{CC} = 2.0 \ V$	1.9	2.0	-	1.9	-	1.9	-	V	
		$I_{O} = -50 \ \mu A; V_{CC} = 3.0 \ V$	2.9	3.0	-	2.9	-	2.9	-	V	
		$I_{O} = -50 \ \mu A; V_{CC} = 4.5 \ V$	4.4	4.5	-	4.4	-	4.4	-	V	
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V	
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.80	-	3.70	-	V	
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$									
	output voltage	$I_{O} = 50 \ \mu A; V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V	
		$I_{O} = 50 \ \mu A; \ V_{CC} = 3.0 \ V$	-	0	0.1	-	0.1	-	0.1	V	
		$I_{O} = 50 \ \mu A; V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V	
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V	
		$I_{O} = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V	
lı	input leakage current	$V_{I} = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to 5.5 V}$	-	-	0.1	-	1.0	-	2.0	μA	
I _{CC}	supply current		-	-	2.0	-	20	-	40	μA	
Cı	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF	
Co	output capacitance		-	4	-	-	-	-	-	pF	

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Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to	o +125 °C	Unit		
			Min	Тур	Max	Min	Max	Min	Max			
74AHCT	30	1										
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V		
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V		
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$									
	output voltage	I _O = -50 μA	4.4	4.5	-	4.4	-	4.4	-	V		
		I _O = -8.0 mA	3.94	-	-	3.80	-	3.70	-	V		
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$										
	output voltage	I _O = 50 μA	-	0	0.1	-	0.1	-	0.1	V		
		l _O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V		
I	input leakage current	$V_1 = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$	-	-	0.1	-	1.0	-	2.0	μA		
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 5.5 \ V \end{array}$	-	-	2.0	-	20	-	40	μA		
Δl _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}$; other pins at V_{CC} or GND; $I_O = 0 \text{ A}$; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA		
Cı	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF		
Co	output capacitance		-	4	-	-	-	-	-	pF		

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	Min	Мах	
74AHC3	0	1								
t _{pd} propagation	A, B, C, D, E, F, G, H to Y; see Figure 7 and 8 [2]									
	delay	V _{CC} = 3.0 V to 3.6 V								
		C _L = 15 pF	-	5.0	9.5	1.0	11.0	1.0	12.0	ns
	l	C _L = 50 pF	-	6.7	12.0	1.0	14.5	1.0	15.5	ns
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	3.6	6.5	1.0	7.5	1.0	8.0	ns
		C _L = 50 pF	-	4.9	8.0	1.0	9.5	1.0	10.5	ns
C _{PD}	power dissipation capacitance	$ f_i = 1 \text{ MHz}; \qquad [3] \\ V_I = \text{GND to } V_{CC} $	-	10	-	-	-	-	-	pF

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Table 8. Dynamic characteristics ... continued

Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 8</u>.

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit	
			Min	Typ[1]	Max	Min	Max	Min	Max]	
74AHCT	30; V _{CC} = 4.5 '	V to 5.5 V									
t _{pd}	propagation	A, B, C, D, E, F, G, H to Y; see Figure 7 and 8 2									
	delay	C _L = 15 pF	-	3.3	6.5	1.0	7.5	1.0	8.0	ns	
		C _L = 50 pF	-	4.7	8.5	1.0	9.5	1.0	10.5	ns	
C _{PD}	power dissipation capacitance	$ f_i = 1 \text{ MHz}; \qquad \qquad \boxed{3} \\ V_I = \text{GND to } V_{CC} $	-	12	-	-	-	-	-	pF	

[1] Typical values are measured at nominal supply voltage ($V_{CC} = 3.3$ V and $V_{CC} = 5.0$ V).

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 $f_i = input frequency in MHz;$

 $f_o = output$ frequency in MHz;

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms

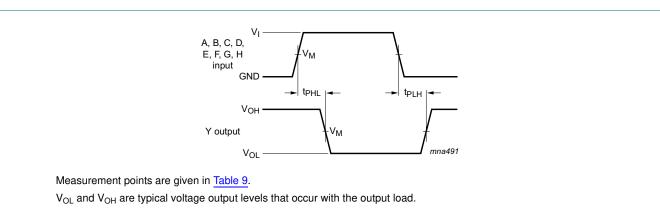


Fig 7. Input to output propagation delays

Table 9.Measurement points

Туре	Input	Output
	V _M	V _M
74AHC30	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74AHCT30	1.5 V	$0.5 \times V_{CC}$

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74AHC30; 74AHCT30

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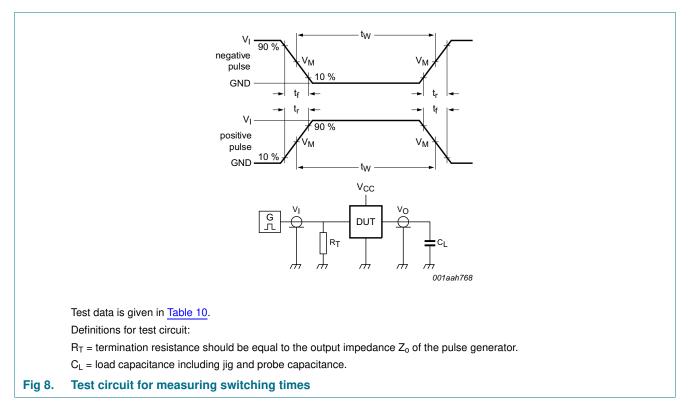


Table 10. Test data

Туре	Input		Load	Test
	VI	t _r , t _f	CL	
74AHC30	V _{CC}	≤ 3.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}
74AHCT30	3.0 V	≤ 3.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}

8-input NAND gate

13. Package outline

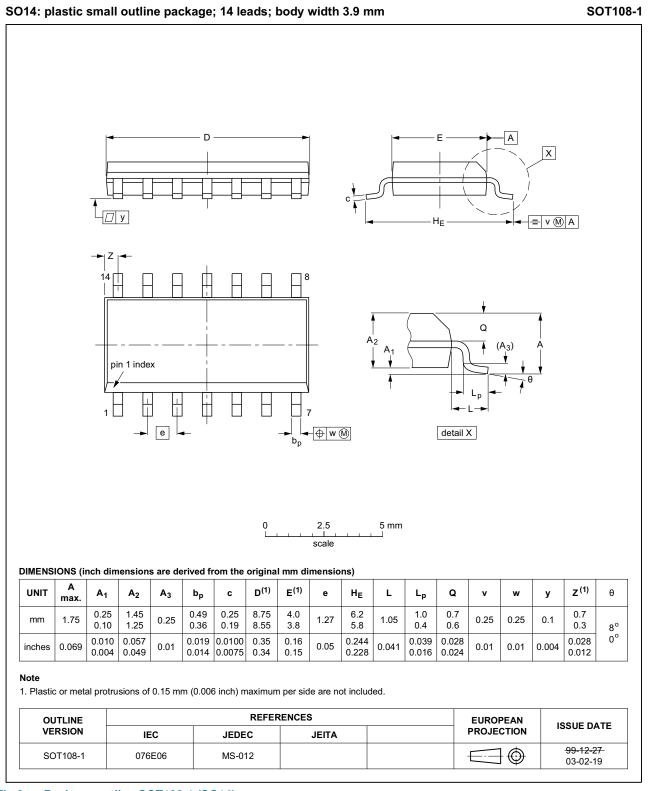


Fig 9. Package outline SOT108-1 (SO14)

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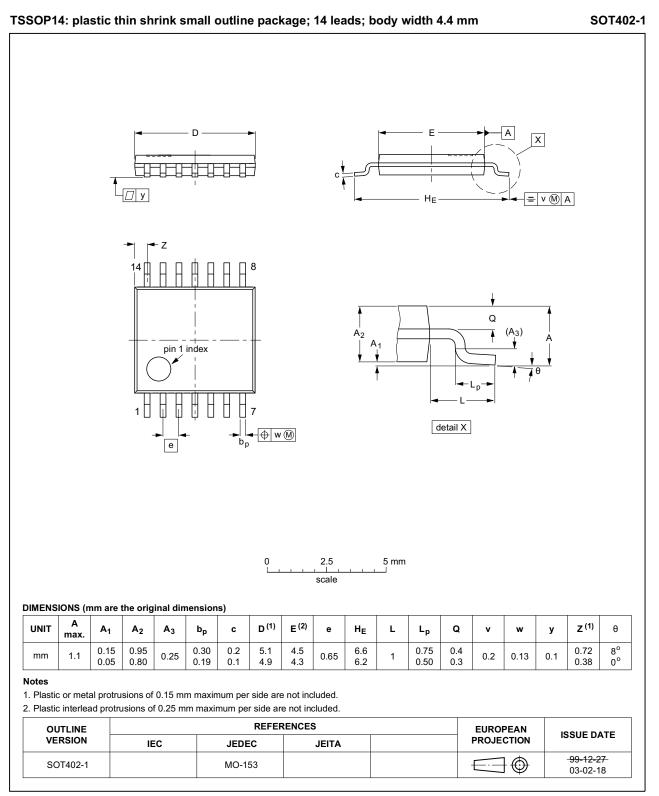
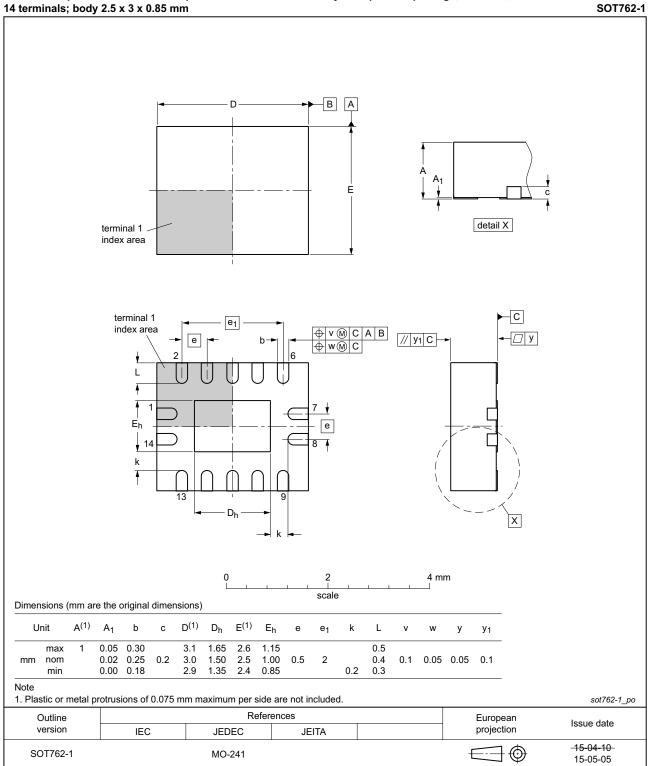


Fig 10. Package outline SOT402-1 (TSSOP14)

8-input NAND gate

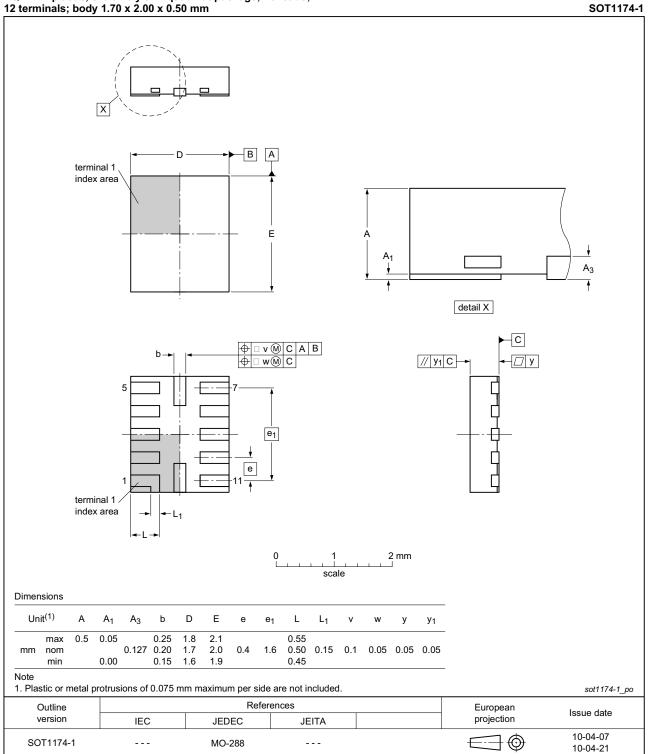


DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads;

Fig 11. Package outline SOT762-1 (DHVQFN14)

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8-input NAND gate



XQFN12: plastic, extremely thin quad flat package; no leads; 12 terminals; body 1.70 x 2.00 x 0.50 mm

Fig 12. Package outline SOT1174-1 (XQFN12)

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14. Abbreviations

Table 11. Abbreviations			
Acronym	Description		
CDM	Charged Device Model		
CMOS	Complementary Metal-Oxide Semiconductor		
DUT	Device Under Test		
ESD	ElectroStatic Discharge		
HBM	Human Body Model		
LSTTL	Low-power Schottky Transistor-Transistor Logic		
ММ	Machine Model		

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
74AHC_AHCT30 v.4	20150722	Product data sheet	-	74AHC_AHCT30 v.3	
Modifications:	Added type number 74AHC30GU12.				
74AHC_AHCT30 v.3	20090626	Product data sheet	-	74AHC_AHCT30 v.2	
Modifications: • Section 3: DHVQFN14 package added.					
	<u>Section 8</u> : derating values added for DHVQFN14 package.				
	• <u>Section 13</u> : c	utline drawing added for DHV	QFN14 package.		
74AHC_AHCT30 v.2	20080530	Product data sheet	-	74AHC_AHCT30 v.1	
74AHC_AHCT30 v.1	19991130	Product specification	-	-	

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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